

## **KSD227**

### **Low Frequency Power Amplifier**

- Complement to KSA642
- Collector Power Dissipation : P<sub>C</sub>=400mW



### 1. Emitter 2. Base 3. Collector

## **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	300	mA
P <sub>C</sub>	Collector Power Dissipation	400	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C=100\mu A, I_E=0$	30			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =25V, $I_E$ =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}=3V$ , $I_{C}=0$			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ =1V, $I_{C}$ =50mA	70		400	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =300mA, I <sub>B</sub> =30mA		0.14	0.4	V

## **h**<sub>FE</sub> Classification

Classification	0	Υ	G
h <sub>FE</sub>	70 ~ 140	120 ~ 240	200 ~ 400

## **Typical Characteristics**

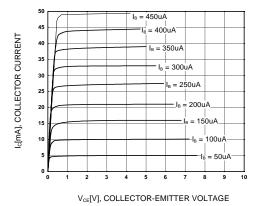
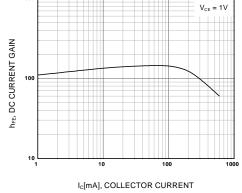


Figure 1. Static Characteristic



1000

Figure 2. DC current Gain

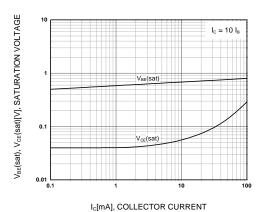


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

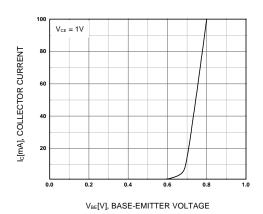


Figure 4. Base-Emitter On Voltage

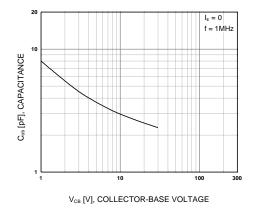


Figure 5. Collector Output Capacitance

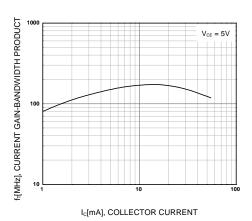
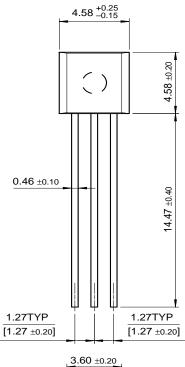


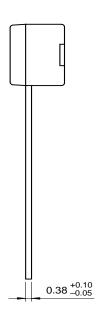
Figure 6. Current Gain Bandwidth Product

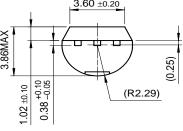
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# **Package Demensions**

TO-92







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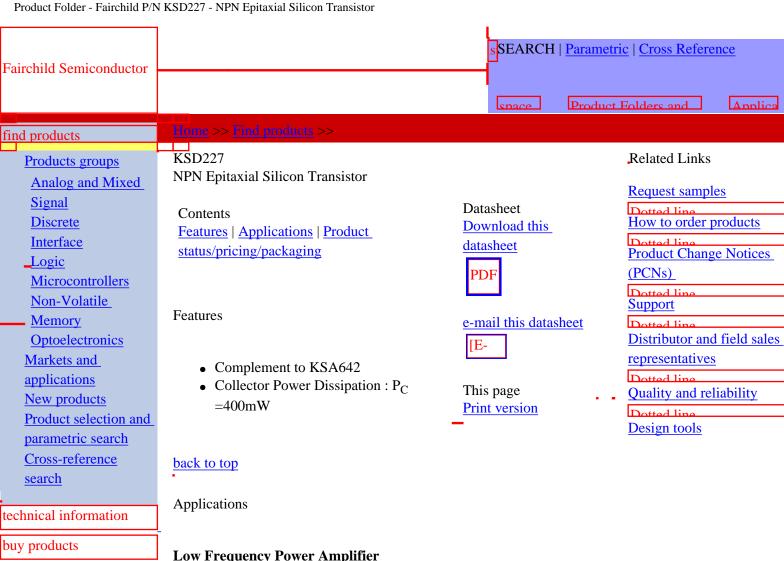
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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
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KSD227YTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL
KSD227GTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL
KSD227GBU	Full Production	\$0.05	TO-92	3	BULK

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